

LAW OFFICES OF  
**McGINN & GIBB, PLLC**

A PROFESSIONAL LIMITED LIABILITY COMPANY  
PATENTS, TRADEMARKS, COPYRIGHTS, AND INTELLECTUAL PROPERTY LAW  
8321 OLD COURTHOUSE ROAD, SUITE 200  
VIENNA, VA 22182-3817  
TELEPHONE: (703) 761-4100  
FACSIMILE/DATA: (703) 761-2375; (703) 761-2376  
E-MAIL: MCGINNGIBB @ AOL.COM

SEAN M. MCGINN  
PHILLIP E. MILLER †  
FREDERICK E. COOPERRIDER †  
PETER A. BALNAVE, Ph.D.  
FREDRIC J. ZIMMERMAN †  
JAMES E. HOWARD †  
KENDAL M. SHEETS  
CHRISTOPHER M. MCGINN\*  
† Other Than Virginia Bar Member  
\* Patent Engineer (Non-attorney)

ANNAPOLIS, MD OFFICE  
FREDERICK W. GIBB, III  
MOHAMMAD S. RAHMAN †  
LAWRENCE A. SCOTT †

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TECHNOLOGY CENTER 2800

April 9, 2003

**VIA FACSIMILE**

To: Examiner Douglas A. Wille  
Group Art Unit No. 2814  
U.S.P.T.O.

Facsimile No.: (703) 872-9319

From: Peter A. Balnave

Facsimile No.: (703) 761-2375

Re: Enclosed § 1.116 Amendment  
U.S. Patent Application Serial No. 09/988,060  
Docket No. F01-273-US DIV

Dear Examiner Wille:

We are enclosing an After-Final Amendment for the above-referenced patent application.

Thank you in advance for your consideration on this case.

Very truly yours,

*Peter A. Balnave*

Peter A. Balnave, Ph.D.

PAB/geb  
Enclosures

Total No. of Pages Transmitted: 6

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4/25/03  
arr

EXPEDITED PROCEDURE  
UNDER 37 C.F.R. 1.116

M. BAUNSON  
7/14/03

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Toshiya UEMURA et al.

Serial No.: 09/988,060

Group Art Unit: 2814

Filed: November 16, 2001

Examiner: Douglas A. Wille

For: A SEMICONDUCTOR LIGHT-EMITTING ELEMENT

Honorable Commissioner of Patents  
Washington, D.C. 20231  
Box AF

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AMENDMENT UNDER 37 C.F.R. §1.116

TECHNOLOGY CENTER 2800

Sir:

In response to the Final Office Action dated January 10, 2003, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 1 and 2 as follows:

1. (Amended) A semiconductor light-emitting element comprising:  
a chip having at least an electrode and a protective film layer;  
an insulating resin for sealing said chip;  
wherein said insulating resin is hardened at high temperature and heat-treated in an atmosphere having relative humidity at a temperature of 60° C or higher.
2. (Amended) A semiconductor light-emitting element according to claim 1, wherein the heat treatment is performed at any temperature in a range from 60° C to 100° C.